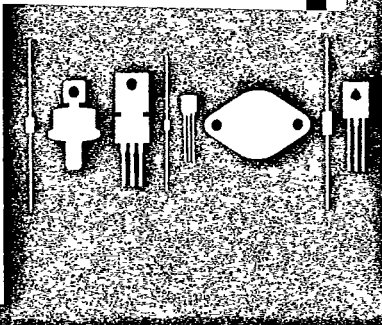


Semiconductor Corp.
Central Semiconductor Corp.
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 145 Adams Avenue
 Hauppauge, New York 11788



MJ12005

NPN SILICON TRANSISTOR

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR MJ12005 type ia a Silicon NPN Power Transistor mounted in a hermetically sealed metal case designed for Horizontal Deflection Circuits.

MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$)

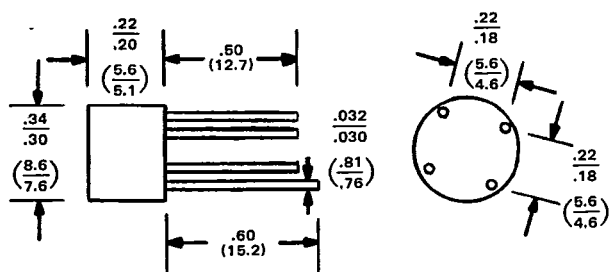
	SYMBOL		UNIT
Collector-Emitter Voltage	V_{CE}	1500	V
Emitter-Base Voltage	V_{EB}	5.0	V
Collector Current	I_C	8.0	A
Emitter Current	I_E	12	A
Base Current	I_B	4.0	A
Power Dissipation	P_D	100	W
Operating and Storage			
Junction Temperature	T_J, T_{STG}	-65 TO +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JC}	1.25	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

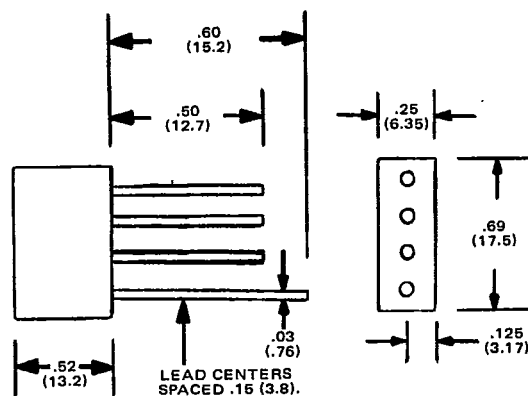
SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{CES}	$V_{CE}=1500\text{V}$		0.25	mA
I_{EBO}	$V_{BE}=5.0\text{V}$		0.1	mA
BV_{CEO}	$I_C=50\text{mA}$	750		V
$V_{CE}(\text{SAT})$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		5.0	V
$V_{BE}(\text{SAT})$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		1.5	V
t_f	$I_C=5.0\text{A}, I_{B1}=1.0\text{A}, L_B=8.0\mu\text{H}$		1.0	μs
$I_{s/b}$	$V_{CE}=50\text{V}, t=1.0\text{s}$	2.0		A

CASE OUTLINE DRAWINGS

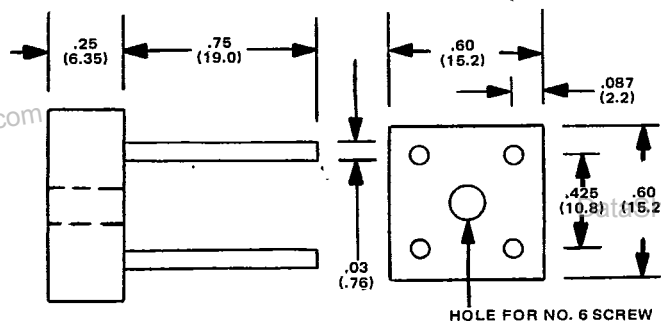
D



CASE A

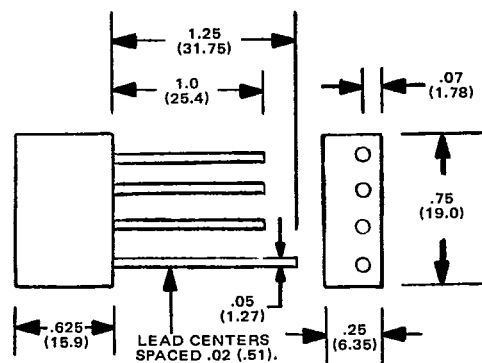
CBR1 Series
CBR2 Series

CASE B

CBR1-L Series
CBR2-L Series

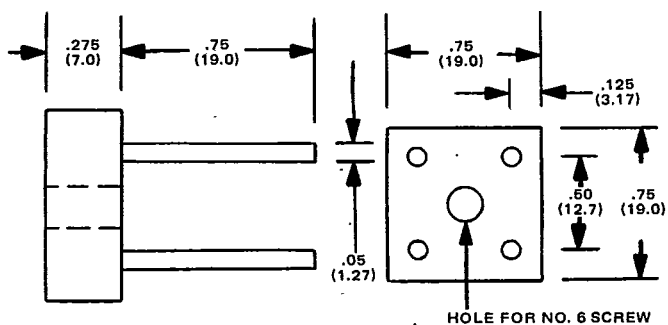
CASE C

CBR3-P Series



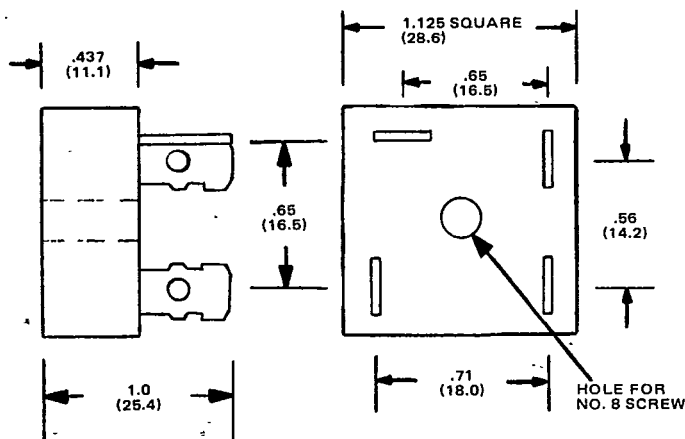
CASE D

CBR4-L Series



CASE E

CBR8 Series



CASE F

CBR10 Series, CBR25 Series
CBR12 Series, CBR30 Series

All Dimensions in Inches (Millimeters)

Drawings Not To Scale

カ

